

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Numerical analysis of the influence of deep energy level traps in SiC Schottky structures

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SIC schottky diode rectifier bridge represented as the diffusion-welded stack

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Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe

Mizsei, Janos; **Korolkov, Oleg; Toompuu, Jana; Mikli, Valdek; Rang, Toomas** Silicon Carbide and Related Materials 2012 : selected peer reviewed papers from the 9th European Conference on Silicon Carbide and Related Materials (ECSCRM 2012), September 2-6, 2012, St. Petersburg, Russian Federation 2013 / p. 677-680 : ill <https://doi.org/10.4028/www.scientific.net/MSF.740-742.677> [Conference Proceedings at Scopus](#) [Article at Scopus](#) [Conference Proceedings at WOS](#) [Article at WOS](#)

The dependence of reverse recovery time on barrier capacitance and series on-resistance in Schottky diodes

Veher, Oleksandr; Sleptšuk, Natalja; Toompuu, Jana; Korolkov, Oleg; Rang, Toomas Materials and contact characterisation VIII 2017 / p. 15-22 : ill <https://doi.org/10.2495/MC170021> [Conference proceedings at Scopus](#) [Article at Scopus](#)